

HEX NON-INVERTING BUFFERS

The HEF4050B provides six non-inverting buffers with high current output capability suitable for driving TTL or high capacitive loads. Since input voltages in excess of the buffers' supply voltage are permitted, the buffers may also be used to convert logic levels of up to 15 V to standard TTL levels. Their guaranteed fan-out into common bipolar logic elements is shown in the table below.

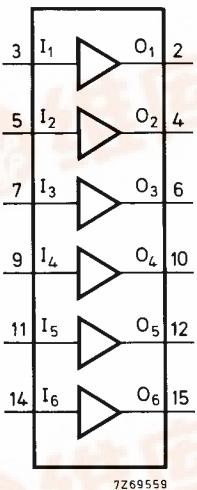


Fig. 1 Functional diagram.

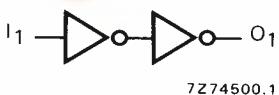


Fig. 3 Logic diagram (one gate).

APPLICATION INFORMATION

Some examples of applications for the HEF4050B are:

- LOCMOS to DTL/TTL converter
- HIGH sink current for driving 2 TTL loads
- HIGH-to-LOW level logic conversion

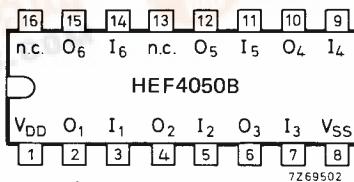


Fig. 2 Pinning diagram.

HEF4050BP : 16-lead DIL; plastic (SOT-38Z).
 HEF4050BD : 16-lead DIL; ceramic (cerdip) (SOT-74).
 HEF4050BT : 16-lead mini-pack; plastic (SO-16; SOT-109A).

Guaranteed fan-out in common logic families

driven element	guaranteed fan-out
standard TTL	2
74LS	9
74L	16

Input protection

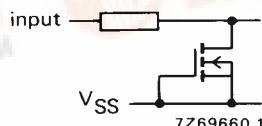


Fig. 4 Input protection circuit that allows input voltages in excess of VDD.

HEF4050B

buffers

D.C. CHARACTERISTICS $V_{SS} = 0 \text{ V}$; $V_I = V_{SS}$ or V_{DD}

HEF	V_{DD} V	V_O V	symbol	$T_{amb}(^{\circ}\text{C})$						
				-40		+25		+85		
				min.	max.	min.	max.	min.	max.	
Output (sink) current LOW	4,75	0,4	I _{OL}	3,5	—	2,9	—	2,3	—	mA
	10	0,5		12,0	—	10,0	—	8,0	—	mA
	15	1,5		24,0	—	20,0	—	16,0	—	mA
Output (source) current HIGH	5	4,6	-I _{OH}	0,52	—	0,44	—	0,36	—	mA
	10	9,5		1,3	—	1,1	—	0,9	—	mA
	15	13,5		3,6	—	3,0	—	2,4	—	mA
Output (source) current HIGH	5	2,5	-I _{OH}	1,7	—	1,4	—	1,1	—	mA

HEC	V_{DD} V	V_O V	symbol	$T_{amb}(^{\circ}\text{C})$						
				-55		+25		+125		
				min.	max.	min.	max.	min.	max.	
Output (sink) current LOW	4,75	0,4	I _{OL}	3,6	—	2,9	—	1,9	—	mA
	10	0,5		12,5	—	10,0	—	6,7	—	mA
	15	1,5		25,0	—	20,0	—	13,0	—	mA
Output (source) current HIGH	5	4,6	-I _{OH}	0,52	—	0,44	—	0,36	—	mA
	10	9,5		1,3	—	1,1	—	0,9	—	mA
	15	13,5		3,6	—	3,0	—	2,4	—	mA

A.C. CHARACTERISTICS $V_{SS} = 0 \text{ V}$; $T_{amb} = 25^{\circ}\text{C}$; $C_L = 50 \text{ pF}$; input transition times $\leq 20 \text{ ns}$

	V_{DD} V	symbol	typ.	max.	typical extrapolation formula
Propagation delays I_n O_n HIGH to LOW	5	t _{PHL}	35	70	26 ns + (0,18 ns/pF)C _L
	10		20	35	16 ns + (0,08 ns/pF)C _L
	15		15	30	12 ns + (0,05 ns/pF)C _L
	LOW to HIGH	t _{PLH}	55	110	28 ns + (0,55 ns/pF)C _L
	10		25	55	14 ns + (0,23 ns/pF)C _L
	15		20	40	12 ns + (0,16 ns/pF)C _L
Output transition times HIGH to LOW	5	t _{THL}	25	50	7 ns + (0,35 ns/pF)C _L
	10		10	20	3 ns + (0,14 ns/pF)C _L
	15		7	14	2 ns + (0,09 ns/pF)C _L
	LOW to HIGH	t _{T LH}	60	120	10 ns + (1,0 ns/pF)C _L
	10		30	60	9 ns + (0,42 ns/pF)C _L
	15		20	40	6 ns + (0,28 ns/pF)C _L

	V_{DD} V	typical formula for P (μW)	where
Dynamic power dissipation per package (P)	5 10 15	$3\,800 f_i + \sum (f_o C_L) \times V_{DD}^2$ $11\,600 f_i + \sum (f_o C_L) \times V_{DD}^2$ $65\,900 f_i + \sum (f_o C_L) \times V_{DD}^2$	f_i = input freq. (MHz) f_o = output freq. (MHz) C_L = load capacitance (pF) $\sum (f_o C_L)$ = sum of outputs V_{DD} = supply voltage (V)